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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/755,164	01/08/2001	Nestor A. Bojarczuk, JR.	YOR9-2000-0642	4431
21254	7590	01/30/2003	EXAMINER QUINTO, KEVIN V	
MCGINN & GIBB, PLLC 8321 OLD COURTHOUSE ROAD SUITE 200 VIENNA, VA 22182-3817			ART UNIT 2826	PAPER NUMBER
DATE MAILED: 01/30/2003				

Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary

Application No.	09/755,164	Applicant(s)	BOJARCUK, ET AL.
Examiner	Kevin Quinto	Art Unit	2826

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133).
- Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

1) Responsive to communication(s) filed on 04 November 2002.

2a) This action is FINAL. 2b) This action is non-final.

3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

4) Claim(s) 1-27 is/are pending in the application.

4a) Of the above claim(s) 19-27 is/are withdrawn from consideration.

5) Claim(s) _____ is/are allowed.

6) Claim(s) 1-18 is/are rejected.

7) Claim(s) _____ is/are objected to.

8) Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

9) The specification is objected to by the Examiner.

10) The drawing(s) filed on _____ is/are: a) accepted or b) objected to by the Examiner.

Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).

11) The proposed drawing correction filed on _____ is: a) approved b) disapproved by the Examiner.

If approved, corrected drawings are required in reply to this Office action.

12) The oath or declaration is objected to by the Examiner.

Priority under 35 U.S.C. §§ 119 and 120

13) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).

a) All b) Some * c) None of:

1. Certified copies of the priority documents have been received.

2. Certified copies of the priority documents have been received in Application No. _____.

3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

* See the attached detailed Office action for a list of the certified copies not received.

14) Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application).

a) The translation of the foreign language provisional application has been received.

15) Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121.

Attachment(s)

1) Notice of References Cited (PTO-892)

2) Notice of Draftsperson's Patent Drawing Review (PTO-948)

3) Information Disclosure Statement(s) (PTO-1449) Paper No(s) _____.

4) Interview Summary (PTO-413) Paper No(s) _____.

5) Notice of Informal Patent Application (PTO-152)

6) Other: _____.

DETAILED ACTION

Response to Arguments

1. Applicant's arguments filed on November 4, 2002, have been fully considered but they are not persuasive.
2. The applicant has stated that the Nishizawa reference (USPN 4,939,571) does not disclose the advantage that the applicant discloses in the present specification. Although Nishizawa does not discuss the e/d ratio, Nishizawa still meets the claimed structure. A similar argument was also applied to the Ma reference (USPN 6,407,435 B1). However such as in the Nishizawa reference, Ma still meets the claimed structure.

Claim Rejections - 35 USC § 112

3. The following is a quotation of the first paragraph of 35 U.S.C. 112:

The specification shall contain a written description of the invention, and of the manner and process of making and using it, in such full, clear, concise, and exact terms as to enable any person skilled in the art to which it pertains, or with which it is most nearly connected, to make and use the same and shall set forth the best mode contemplated by the inventor of carrying out his invention.
4. Claims 8-10, 12, and 13 are rejected under 35 U.S.C. 112, first paragraph, because the specification, while being enabling for a composite insulating layer with two dielectric layers, does not reasonably provide enablement for a composite insulating layer with three dielectric layers. The specification does not enable any person skilled in the art to which it pertains, or with which it is most nearly connected, to make or use the invention commensurate in scope with these claims.

5. Claims 8-10, 12 and 13 appear to be claiming a composite insulating layer with three dielectric layers. However the specification appears to support only a two layer dielectric structure.

Claim Rejections - 35 USC § 102

6. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless –

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

(e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.

7. Claims 1-7, 11, and 14-18 are rejected under 35 U.S.C. 102(b) as being anticipated by Nishizawa et al. (USPN 4,939,571).

8. In reference to claim 1, Nishizawa et al. (USPN 4,939,571, hereinafter referred to as the "Nishizawa" reference) discloses a similar device. Figure 1 of Nishizawa discloses a field effect transistor having a substrate (5), a source (1), a drain (3) and a channel region (2). There is an insulating layer (6) disposed over the channel region (2). There is a gate electrode (4) which is disposed over the insulating layer (6).

Nishizawa discloses that the composite insulating layer (6) contains aluminum nitride and aluminum oxide (column 2, lines 9-11).

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9. With regard to claim 2, Nishizawa discloses (in column 2, lines 9-11) that the insulating layer (6) is made with "SiO₂, Al₂O₃, Si₃N₄, or AlN, or their mixture, or their composite insulating layer." The examiner believes that this phrase covers every combination of the stated four dielectric layers. Thus it is the examiner's belief that this phrase meets the applicant's limitation where the aluminum nitride is "disposed over said aluminum oxide."

10. In reference to claims 3 and 11, Nishizawa discloses (in column 2, lines 9-11) that the insulating layer (6) is made with "SiO₂, Al₂O₃, Si₃N₄, or AlN, or their mixture, or their composite insulating layer." It is the examiner's belief that this phrase meets the applicant's limitation where the aluminum nitride is "disposed under said aluminum oxide."

11. With regard to claim 4, Nishizawa discloses (in column 2, lines 9-11) that the insulating layer (6) is made with "SiO₂, Al₂O₃, Si₃N₄, or AlN, or their mixture, or their composite insulating layer." It is the examiner's belief that this phrase meets the applicant's limitation where a layer of silicon dioxide is "disposed upon said channel region, said aluminum nitride disposed over said silicon dioxide."

12. In reference to claim 5, Nishizawa discloses (in column 2, lines 9-11) that the insulating layer (6) is made with "SiO₂, Al₂O₃, Si₃N₄, or AlN, or their mixture, or their composite insulating layer." It is the examiner's belief that this phrase meets the applicant's limitation where a layer of silicon dioxide is "disposed over said channel region, said aluminum nitride disposed under said silicon dioxide."

13. In reference to claim 6, Nishizawa discloses (in column 2, lines 9-11) that the insulating layer (6) is made with "SiO₂, Al₂O₃, Si₃N₄, or AlN, or their mixture, or their composite insulating layer." It is the examiner's belief that this phrase meets the applicant's limitation where a layer of silicon nitride is "disposed upon said channel region, said aluminum nitride disposed over said silicon nitride."

14. In reference to claim 7, Nishizawa discloses (in column 2, lines 9-11) that the insulating layer (6) is made with "SiO₂, Al₂O₃, Si₃N₄, or AlN, or their mixture, or their composite insulating layer." It is the examiner's belief that this phrase meets the applicant's limitation where a layer of silicon nitride is "disposed over said channel region, said aluminum nitride disposed under said silicon nitride."

15. In reference to claim 14, Nishizawa discloses a similar device. Figure 1 of Nishizawa discloses a field effect transistor having a substrate (5), a source (1), a drain (3) and a channel region (2). There is an insulating layer (6) disposed over the channel region (2). There is a gate electrode (4) which is disposed over the insulating layer (6). Nishizawa discloses (in column 2, lines 9-11) that the insulating layer (6) is made with "SiO₂, Al₂O₃, Si₃N₄, or AlN, or their mixture, or their composite insulating layer." The examiner believes that this phrase covers every combination of the stated four dielectric layers. Therefore it is the examiner's belief that this phrase meets the applicant's limitation where there is a "first layer comprising aluminum oxide disposed upon said channel region and a second layer comprising aluminum nitride is disposed upon said first layer."

16. In reference to claims 15 and 16, Nishizawa discloses a similar device. Figure 1 of Nishizawa discloses a field effect transistor having a substrate (5), a source (1), a drain (3) and a channel region (2). There is an insulating layer (6) disposed over the channel region (2). There is a gate electrode (4) which is disposed over the insulating layer (6). Nishizawa discloses that the insulating layer (6) contains aluminum nitride (column 2, lines 9-11).

17. In reference to claims 17 and 18, Nishizawa discloses such a multi-terminal device. Figure 1 of Nishizawa discloses a field effect transistor having a substrate (5), a source (1), a drain (3) and a channel region (2). There is an insulating layer (6) disposed over the channel region (2). There is a gate electrode (4) which is disposed over the insulating layer (6). Nishizawa discloses that the insulating layer (6) contains aluminum nitride (column 2, lines 9-11).

18. Claims 1, 2, 6, and 14-18 are rejected under 35 U.S.C. 102(e) as being anticipated by Ma et al. (USPN 6,407,435 B1).

19. In reference to claim 1, Ma et al. (USPN 6,407,435 B1, hereinafter referred to as the "Ma" reference) discloses a similar device. Figure 2 of Ma discloses a field effect transistor having a substrate (112), a source (not labeled), a drain (not labeled) and a channel region (114). There is an insulating layer (130) disposed over the channel region (114). There is a gate electrode (118) which is disposed over the insulating layer (130). Ma discloses that the insulating layer (130) is aluminum nitride (column 4, lines 32-35).

20. In reference to claim 2, figure 4 of Ma describes a similar device. Figure 4 shows a field effect transistor having a substrate (112), a source (not labeled), a drain (not labeled) and a channel region (114). There is a first insulating layer (170) and a second insulating layer (130) disposed over the channel region (114). There is a gate electrode (118) which is disposed over the second insulating layer (130). Ma states that the first insulating layer (170) can be aluminum oxide (column 4, lines 66-67 and column 5, lines 1-4). Ma states that the second insulating layer (130) can be aluminum nitride (column 4, lines 32-35).

21. In reference to claim 6, Ma states that the first insulating layer (170) can be silicon nitride (column 4, lines 66-67 and column 5, lines 1-4). Ma states that the second insulating layer (130) can be aluminum nitride (column 4, lines 32-35).

22. In reference to claim 14, figure 4 of Ma describes a similar device. Figure 4 shows a field effect transistor having a substrate (112), a source (not labeled), a drain (not labeled) and a channel region (114). There is a first insulating layer (170) and a second insulating layer (130) disposed over the channel region (114). There is a gate electrode (118) which is disposed over the second insulating layer (130). Ma states that the first insulating layer (170) can be aluminum oxide (column 4, lines 66-67 and column 5, lines 1-4). Ma states that the second insulating layer (130) can be aluminum nitride (column 4, lines 32-35).

23. In reference to claims 15 and 16, Ma discloses a similar device. Figure 2 of Ma discloses a field effect transistor having a substrate (112), a source (not labeled), a drain (not labeled) and a channel region (114). There is an insulating layer (130)

disposed over the channel region (114). There is a gate electrode (118) which is disposed over the insulating layer (130). Ma discloses that the insulating layer (130) is aluminum nitride (column 4, lines 32-35):

24. In reference to claims 17 and 18, Ma discloses such a multi-terminal device.

Figure 2 of Ma discloses a field effect transistor having a substrate (112), a source (not labeled), a drain (not labeled) and a channel region (114). There is an insulating layer (130) disposed over the channel region (114). There is a gate electrode (118) which is disposed over the insulating layer (130). Ma discloses that the insulating layer (130) is aluminum nitride (column 4, lines 32-35).

25. Claims 1, 4, and 15-18 are rejected under 35 U.S.C. 102(b) as being anticipated by Yamazaki (USPN 5,094,966).

26. With regard to claims 1, 4, and 15-18, Yamazaki (USPN 5,094,966) discloses a similar device. Figure 1 of Yamazaki illustrates a multi-terminal device in the form of a field effect transistor which has a substrate (1), a source (6), a drain (7) and a channel region (not labeled). There is an insulating layer (5a, 5b) disposed over the channel region. There is a gate electrode (4) which is disposed over the insulating layer (5a, 5b). Yamazaki discloses (column 4, lines 46-50) that the insulating layer (5a, 5b) is made of one layer of silicon dioxide (5a) and a layer of aluminum nitride (5b).

27. Claims 1, 3, 4, 7, 11, and 14-18 are rejected under 35 U.S.C. 102(b) as being anticipated by Goldman et al. (USPN 4,151,537).

28. With regard to claims 1, 4, and 15-18, Goldman et al. (USPN 4,151,537, hereinafter referred to as the "Goldman" reference) discloses a similar device. Goldman

illustrates a multi-terminal device in the form of a field effect transistor which has a substrate (12), a source (14), a drain (16) and a channel region (18). There is an insulating layer (22, 24, 26) disposed over the channel region (18). There is a gate electrode (28) which is disposed over the insulating layer (22, 24, 26). Goldman states (column 2, lines 61-65) that the top insulating layer (22) can be silicon nitride, the middle insulating layer (24) can be silicon oxynitride, and the bottom insulating layer (26) can be silicon dioxide. However, Goldman also discloses (column 2, lines 65-68) that any of the layers of the insulating layer (22, 24, 26) can be made of aluminum nitride or aluminum oxide; thereby meeting claims 1, 4, and 15-18.

29. In reference to claim 2, the examiner believes that the device of Goldman (in column 2, lines 61-68) meets the applicant's limitation where the aluminum nitride is "disposed over said aluminum oxide."

30. In reference to claims 3 and 11, the examiner believes that the device of Goldman (in column 2, lines 61-68) meets the applicant's limitation where the aluminum nitride is "disposed under said aluminum oxide."

31. With regard to claim 4, the examiner believes that the device of Goldman (in column 2, lines 61-68) meets the applicant's limitation where a layer of silicon dioxide is "disposed upon said channel region, said aluminum nitride disposed over said silicon dioxide."

32. In reference to claim 7, the examiner believes that the device of Goldman (in column 2, lines 61-68) meets the applicant's limitation where a layer of silicon nitride is

"disposed over said channel region, said aluminum nitride disposed under said silicon nitride."

33. In reference to claim 14, Goldman discloses a similar device. Goldman illustrates a field effect transistor which has a substrate (12), a source (14), a drain (16) and a channel region (18). There is an insulating layer (22, 24, 26) disposed over the channel region (18). There is a gate electrode (28) which is disposed over the insulating layer (22, 24, 26). Goldman states (column 2, lines 61-65) that the top insulating layer (22) can be silicon nitride, the middle insulating layer (24) can be silicon oxynitride, and the bottom insulating layer (26) can be silicon dioxide. However, Goldman also discloses (column 2, lines 65-68) that any of the layers of the insulating layer (22, 24, 26) can be made of aluminum nitride or aluminum oxide. Therefore, the examiner believes that the device of Goldman (in column 2, lines 61-68) meets the applicant's limitation where there is a "first layer comprising aluminum oxide disposed upon said channel region and a second layer comprising aluminum nitride is disposed upon said first layer."

Double Patenting

34. Claim 11 is objected to under 37 CFR 1.75 as being a substantial duplicate of claim 3. When two claims in an application are duplicates or else are so close in content that they both cover the same thing, despite a slight difference in wording, it is proper after allowing one claim to object to the other as being a substantial duplicate of the allowed claim. See MPEP § 706.03(k).

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Kevin Quinto whose telephone number is (703) 306-5688. The examiner can normally be reached on M-F 8AM-5PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nathan Flynn can be reached on (703) 308-6601. The fax phone numbers for the organization where this application or proceeding is assigned are (703) 308-7722 for regular communications and (703) 308-7724 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

KVQ

January 26, 2003



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